

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	160	((access\$3 isolat\$3 buffer) near3 (circuit transistor)) and (isolat\$3 near3 well) and (external\$2 with test\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 14:00
S2	279	365/72.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 13:26
S3	3282	365/201.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 13:30
S4	493	365/175.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 13:31
S5	890	365/177.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 13:40
S6	500	257/499.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 13:40
S7	350	257/544.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 13:40
S8	10	S1 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 13:42

S9	1	(S2 or S4 or S5) and (S6 or S7)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 13:41
S10	0	S8 and S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 13:41
S11	0	S1 and S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 13:42
S12	0	(S2 or S4 or S5) and S3 and (isolated near3 well)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 13:43
S13	12	(S2 or S4 or S5) and (isolated near3 well)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 14:14
S14	7	S13 and (access isolat\$3 buffer) near3 (transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 13:43
S15	37	((access\$3 isolat\$3 buffer) near3 (circuit transistor)) same (isolat\$3 near3 well) and (external\$2 with test\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 14:22
S16	28	((access\$3 isolat\$3 buffer) near3 (circuit transistor)) with (isolat\$3 near3 well) and (external\$2 with test\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 14:23

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L9	1	((access near3 circuit) and (first adj3 transistor) and (second adj3 transistor) and (isolat\$3 near3 well) and (first adj3 diode) and (second adj3 diode)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 16:40